

App. Serial No 10/539,280  
Docket No.: BE020045US

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SEP 07 2007

**In the Claims:**

Please amend claims 1, 4 and 6-8 as indicated below. This listing of claims replaces all prior versions.

1. (*Currently amended*) A method of manufacturing a semiconductor device with a semiconductor body, the semiconductor device including and a substrate and comprising, at least one semiconductor element, ~~the semiconductor device that~~ is equipped with at least one connection region and connected to a superjacent strip-shaped connection conductor ~~connected to the connection region,~~ the connection region and the superjacent strip-shaped connection conductor are both being recessed in a dielectric layer, and the method comprising:

providing a first material in a dielectric region ~~of a first material is provided on~~ the semiconductor body ~~at the a location of the connection region to be formed,~~ the first material being made of an organic material and the first material having a decomposition temperature;

coating the dielectric region is coated with [[a]] the dielectric layer, the dielectric layer being made of a second material having a decomposition temperature that is higher than the decomposition temperature of the first material; ~~that differs from the first material,~~

removing the first material by heating the semiconductor device to a temperature that is above the decomposition temperature of the first material yet below the decomposition temperature of the second material;

after removing the first material, etching the said dielectric layer is provided, at the location of the strip-shaped connection conductor to be formed, with to form a strip-shaped recess viewed in projection, that overlaps the dielectric region and extends up to said the dielectric region;[[.]]

~~and after the formation of the strip-shaped recess and the removal of the dielectric region,~~

forming the connection region is formed by depositing an electroconductive material in a space obtained by the removal of the first material; dielectric region, and

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forming the superjacent strip-shaped connection conductor is formed by depositing an electroconductive material in the strip-shaped recess, characterized in that  
~~for the first material use is made of an organic material, and~~  
~~for the second material use is made of a material having a higher decomposition temperature than the organic material, and~~  
~~the dielectric region is removed by heating at a temperature above the decomposition temperature of the organic material yet below the decomposition temperature of the second material.~~

2. *(Previously presented)* A method as claimed in claim 1, characterized in that  
a photoresist is used as the first material, and  
a dielectric resin having a higher decomposition temperature than the photoresist is used as the second material.

3. *(Previously presented)* A method as claimed in claim 1, characterized in that  
a photoresist is used as the first material, and a liquid glass is used as the second material, said liquid glass is converted to solid glass by heating.

4. *(Currently amended)* A method as claimed in claim 2, characterized in that  
the ~~dielectric region~~ first material is removed during a thermal treatment of the semiconductor body wherein the liquid glass is converted to solid glass.

5. *(Previously presented)* A method as claimed in claim 1, characterized in that  
the first material as well as the second material are applied in liquid state to the semiconductor body with a centrifuging process.

6. *(Currently amended)* A method as claimed in claim 1, characterized in that  
the dielectric region is formed by applying a further dielectric layer, covering part of the further dielectric layer with above which a mask, and is provided removing the part of outside which the further dielectric layer not covered by the mask is removed by means of etching: [[.]] and

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the dielectric layer, ~~after deposition,~~ is covered with a mask ~~which is provided~~ with having an aperture at ~~the~~ a location of where the strip-shaped recess will to be formed, after which the strip-shaped recess is formed by means of etching.

7. (*Currently amended*) A method as claimed in claim 1, characterized in that after removal of the first material dielectric region and after formation of the strip-shaped recess, yet before deposition of the conductive material, the semiconductor body is cleaned.

8. (*Currently amended*) A method as claimed in claim 1, characterized in that copper is used as the electroconductive material, and prior to the deposition of the copper, an electroconductive layer is deposited, at ~~the location of the connection region to be~~ being formed on the electroconductive layer, said electroconductive layer forms a barrier for copper.

9. (*Previously presented*) A method as claimed in claim 8, characterized in that the electroconductive layer is applied by means of a physical vapor deposition process, and the copper is provided by means of an electroplating process.

10. (*Previously presented*) A semiconductor device obtained by the method of claim 1.